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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re application of

Docket No: Q64215

Yoshihiro HAYASHI, et al.

Appln. No.: 09/838,343

Group Art Unit: 2811

Confirmation No.: 1069

Examiner: Unknown

Filed: April 20, 2001

For: METHOD FOR VAPORIZATION OF LIQUID ORGANIC FEEDSTOCK AND
METHOD FOR GROWTH OF INSULATION FILM

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**INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. §§ 1.97 and 1.98**

Commissioner for Patents
Washington, D.C. 20231

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

1. Japanese Unexamined Patent Publication No. 3-8330, published January 16, 1991.
2. Japanese Unexamined Patent Publication No. 2000-012532. (This reference was previously submitted to the Patent and Trademark Office with an IDS dated August 7, 2001 and therefore a copy is not being enclosed herewith.)
3. Japanese Unexamined Patent Publication No. 8-288242, published November 11, 1996.
4. Japanese Unexamined Patent Publication No. 5-175134, published July 13, 1993.

One copy of each of the listed documents is submitted herewith.

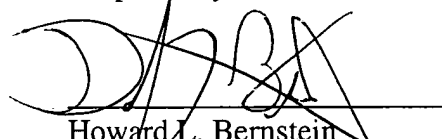
Y. HAYASHI
Appln. No. 09/838,343
Information Disclosure Statement

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date for an application other than a continued prosecution application (CPA) under §1.53(d); (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant encloses herewith a copy of a Japanese Office Action dated October 9, 2002 with an English translation of the pertinent portion thereof which cites such documents and indicates the degree of relevance found by the foreign patent office.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

Respectfully submitted,


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WASHINGTON OFFICE



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PATENT TRADEMARK OFFICE

Date: January 9, 2003



Ref. # Q64215

The invention related to the following claims of this application is based on inventions cited in the following publications, which had been circulated prior to this application in Japan or a foreign country. Because a person having ordinary knowledge in the technical field to which that invention belongs could have easily made the invention prior to this application, a patent cannot be granted pursuant to the stipulations of Article 29, Section 2 of the Japan Patent Law.

Description (For the cited literature, see the List of Cited Literature.)

- Claims 1 to 6
- Cited Literature 1 to 4
- Remarks:

A person skilled in the art could easily use the divinyl siloxane bisbenzocyclobutene monomer described in Cited Example 2 as the liquid semiconductor molding material in the invention described in Cited Example 1.

The aerosol diameter and flow rate of the carrier gas are design matters, and a person skilled in the art could easily obtain suitable levels by experimentation, etc.

A person skilled in the art could easily conceive of directly connecting the gasification equipment to the reaction chamber. (Fig. 6 of Cited Example 3; drawings of Cited Example 4)

List of Cited Literature

1. Japanese Unexamined Patent Application Publication H03-008330
2. Japanese Unexamined Patent Application Publication 2000-012532
3. Japanese Unexamined Patent Application Publication H08-288242
4. Japanese Unexamined Patent Application Publication H05-175134

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